

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| S1 | 2 | ("5656514").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/19 09:07 |
| S2 | 2142 | (@ad<"20040921" or @rlad<"20040921") and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/19 13:45 |
| S3 | 1258 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/22 15:20 |
| S4 | 25 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "first base" and "second base" and "first emitter" and "second emitter" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/22 15:49 |

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| S7 | 345 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/23 10:23 |
| S9 | 10 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "first base" and "second base" and "first emitter" and "second emitter" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/22 15:50 |
| S12 | 42 | (@ad<"20040921" or @rlad<"20040921") and (("4319932" "4967254" "5006912" "5063427" "5106767" "5323032" "5346840" "5389803").PN. OR ("5656514"). URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/01/22 16:18 |
| S18 | 17 | (@ad<"20040921" or @rlad<"20040921") and (("4583106" "5065209" "5073810" "5117271" "5198375" "5315151" "5321301" "5323032").PN. OR ("5508553"). URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/01/23 09:07 |

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| S19 | 11 | (@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "sic base" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/23 10:24 |
| S20 | 2 | "6967144" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/01/23 10:42 |
| S22 | 19 | (@ad<"20040921" or @rlad<"20040921") and (("4985742" "5010382" "5122845" "5326992" "5378921" "5408120").PN. OR ("5641975"). URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/01/23 12:59 |
| S23 | 403 | (@ad<"20040921" or @rlad<"20040921") and 257/198. ccls. and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer) | US-PGPUB; USPAT; USOCR | OR | ON | 2007/01/23 13:05 |